

LS5018B LS5060B/LS5120B

 $\mathsf{TRISIL}^\mathsf{TM}$

FEATURES

- BIDIRECTIONAL CROWBAR PROTECTION.
- BREAKDOWN VOLTAGES RANGE: 18V, 60V and 120V.
- HOLDING CURRENT = 200mA min.
- HIGH SURGE CURRENT CAPABILITY IPP = 100A 10/1000 μs

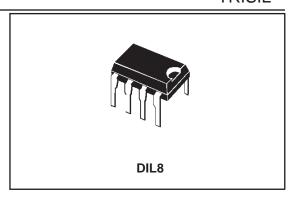
DESCRIPTION

very low.

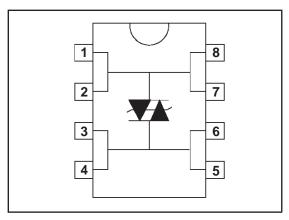
The LS50xxB series has been designed to protect telecommunication equipment against lightning and transients induced by AC power lines. Its high surge current capability makes the LS50xxB a reliable protection device for very exposed equipment, or when series resistors are

COMPLIES WITH THE FOLLOWING STANDARDS:

CCITT K17 - K20	10/700	μs	1.5 kV
	5/310	μs	38 A
VDE 0433	10/700	μs	2 kV
	5/200	μs	50 A
CNET	0.5/700	μs	1.5 kV
	0.2/310	μs	38 A



SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS (Tamb =25°C)

Symbol	Parameter	Value	Unit	
lpp	Peak pulse current	10/1000 μs 8/20 μs	100 250	А
Ітѕм	Non repetitive surge peak on-state current	tp = 20 ms	50	А
dl/dt	Critical rate of rise of on-state current	Non repetitive	100	A/μs
dV/dt	Critical rate of rise of off-state voltage V _{RM}		5	kV/μs
T _{stg} Tj	Storage and operating junction temperature range		- 40 to + 150 150	°C °C
T∟	Maximum lead temperature for soldering	230	°C	

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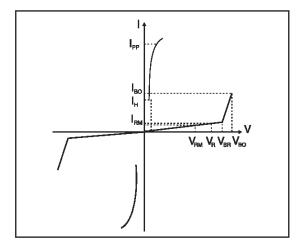
LS5018B/LS5060B/LS5120B

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction to ambient on printed circuit with recommended pad layout	80	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} =25°C)

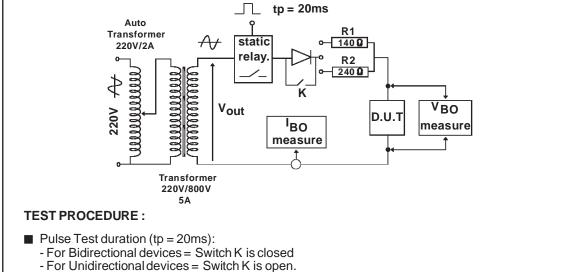
Symbol	Parameter			
Irm	Leakage current at stand-offvoltage			
V _{RM}	Stand-offvoltage			
V_{BR}	Breakdownvoltage			
V _{BO}	Breakover voltage			
Ін	Holding current			
I _{BO}	Breakover current			
I _{PP}	Peak pulse current			
С	Capacitance			



	I _{RM} @	V _{RM}	V _{BR}	@ I R	V _{BO}	@ I _{BO}	I _H	С
Туре	max.		min.		max.	typ.	min.	max.
71.					note 1		note 2	note 3
	μ Α	٧	٧	mA	٧	mA	mA	рF
LS5018B	5	16	17	1	22	1300	200	150
LS5060B	10	50	60	1	85	1000	200	150
LS5120B	20	100	120	1	180	1250	250	150

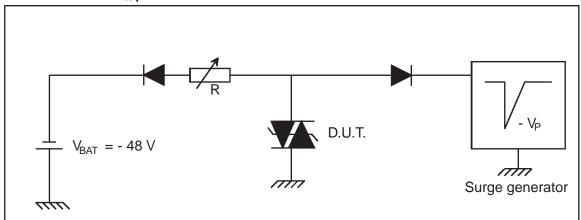
Note 1 : Measured at 50Hz (1 cycle)
Note 2 : See test circuit
Note 3 : V_R = 5 V, F = 1MHz.

TEST CIRCUIT 1 FOR IBO and VBO parameters:



- Vour Selection
 - Device with V_{BO} < 200 Volt
 - Vout = 250 V_{RMs}, R₁ = 140 Ω . Device with V_{BO} \geq 200 Volt
 - - Vout = 480 V_{RMS}, R_2 = 240 Ω .

TEST CIRCUIT 2 for I_H parameter.



This is a GO-NOGO Test which allows to confirm the holding current (IH) level in a functional test circuit.

TEST PROCEDURE:

- 1) Adjust the current level at the I_H value by short circuiting the AK of the D.U.T.
 - 2) Fire the D.U.T with a surge Current : Ipp = 10A, $10/1000 \mu s$.
 - 3) The D.U.T will come back off-state within 50 ms max.

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Figure 1 : Non repetitive surge peak current versus overload duration

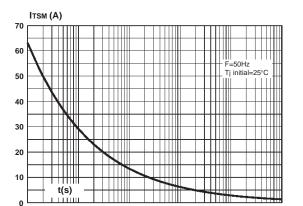


Figure 3: Relative variation of breakdown voltage versus ambient temperature.

1E+1

1E+2

1E+3

1E+0

1E-1

1E-2

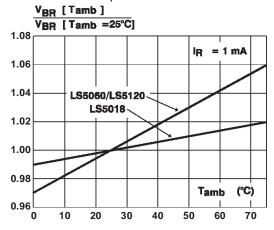


Figure 2: Relative variation of holding current versus junction temperature.

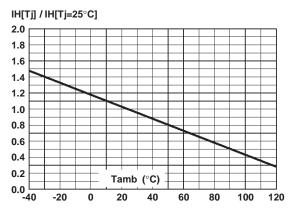
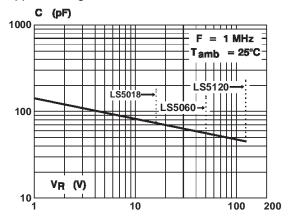
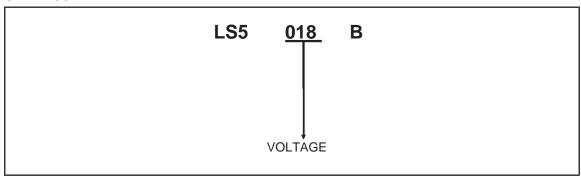


Figure 4: Junction capacitance versus reverse applied voltage.



ORDER CODE



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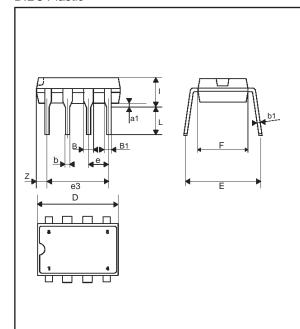
MARKING: Logo, Date Code, part Number.

Packaging: Products supplied in antistatic tubes.

Weight: 0.59g

PACKAGE MECHANICAL DATA

DIL 8 Plastic



	DIMENSIONS					
REF.	Millimetres		es		3	
	Min.	Тур.	Max.	Min.	Тур.	Max.
a1	0.70			0.027		
В	1.39		1.65	0.055		0.065
B1	0.91		1.04	0.036		0.041
b		0.5			0.020	
b1	0.38		0.50	0.015		0.020
D			9.80			0.385
Е		8.8			0.346	
е		2.54			0.100	
е3		7.62			0.300	
F			7.1			0.280
I			4.8			0.189
L		3.3			0.130	
Z	0.44		1.60	0.017		0.063

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